

ABSTRACT

A method and system for providing a semiconductor device is disclosed. The semiconductor device includes a first layer to be etched. The method and system include depositing an antireflective coating (ARC). At least a portion of the ARC layer is on the first layer. The method and system also include patterning a resist layer. The resist layer includes a pattern having a plurality of apertures therein. The resist layer is for etching the first layer. A first portion of the first layer and a second portion of the ARC layer are exposed by the pattern. The method and system also include etching the first portion of the first layer and the second portion of the ARC layer and removing the resist layer utilizing a plasma etch. The ARC layer is resistant to the plasma etch.

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